

**10N70Z-Q**

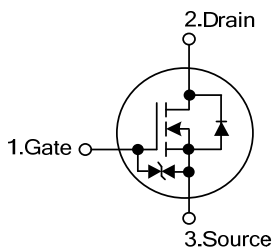
Preliminary

Power MOSFET**10A, 700V N-CHANNEL
POWER MOSFET**■ **DESCRIPTION**

The **UTC 10N70Z-Q** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ **FEATURES**

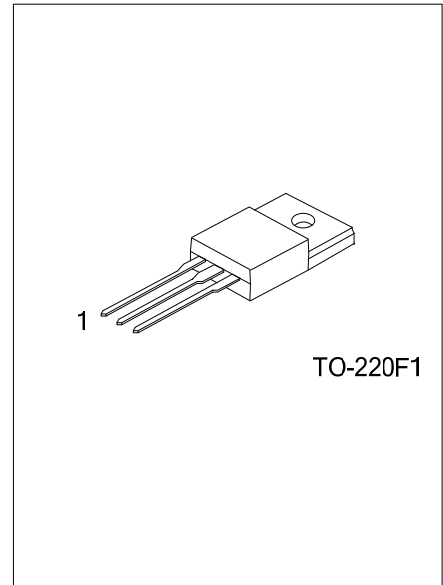
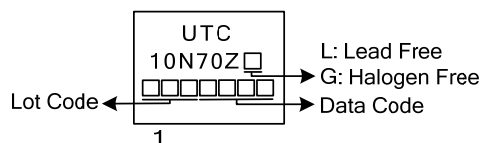
- * $R_{DS(ON)} < 1.2\Omega @ V_{GS} = 10V$
- * Fast switching
- * 100% avalanche tested
- * Improved dv/dt capability

■ **SYMBOL**■ **ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N70ZL-TF1-T	10N70ZG-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) T: Tube (2) TF1: TO-220F1 (3) L: Lead Free, G: Halogen Free
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■ **MARKING**

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 20	V
Avalanche Current (Note 2)		I_{AR}	10	A
Drain Current	Continuous	I_D	10	A
	Pulsed (Note 2)	I_{DM}	40	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	250	mJ
	Repetitive (Note 2)	E_{AR}	15.6	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		P_D	50	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 5\text{mH}$, $I_{AS} = 10\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$ Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 9.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.5	$^\circ\text{C}/\text{W}$

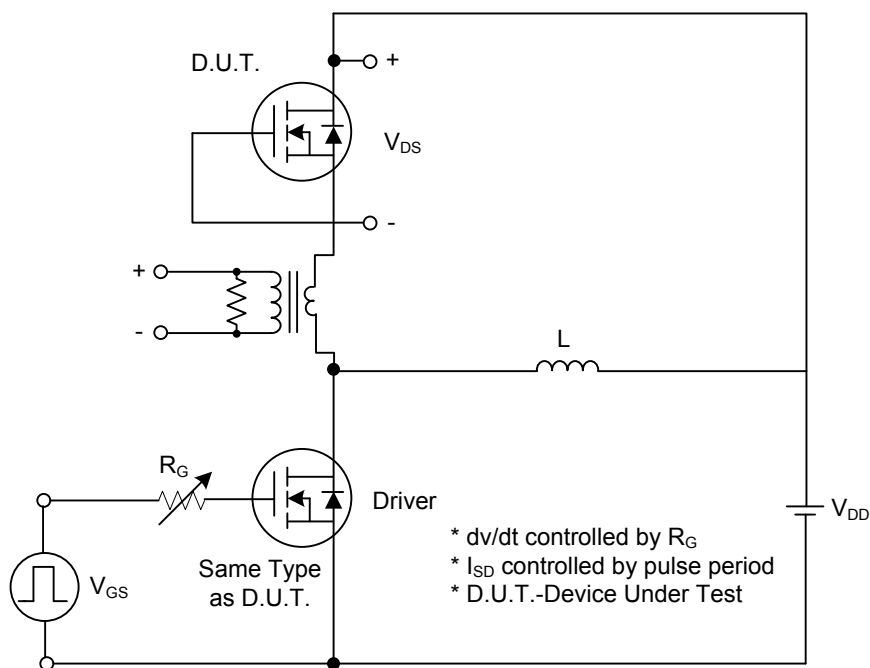
■ ELECTRICAL CHARACTERISTICS($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	700			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 700V, V _{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 20 V, V _{DS} = 0 V			5	μA
	Reverse		V _{GS} = -20 V, V _{DS} = 0 V			-5	μA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D = 250 μA, Referenced to 25°C		0.7		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 5A		1.0	1.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		890	1290	pF
Output Capacitance		C _{OSS}			120	160	pF
Reverse Transfer Capacitance		C _{RSS}			14	22	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	V _{DS} =30V, I _D =0.5A, R _G =25Ω (Note 1, 2)		54	70	ns
Turn-On Rise Time		t _R			69	150	ns
Turn-Off Delay Time		t _{D(OFF)}			290	340	ns
		t _F			95	145	ns
Total Gate Charge		Q _G	V _{DS} =50V, I _D =1.3A, V _{GS} =10 V (Note 1, 2)		39	57	nC
Gate-Source Charge		Q _{GS}			7.9		nC
Gate-Drain Charge		Q _{GD}			9.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} = 0 V, I _S =10A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I _S				10	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				40	A

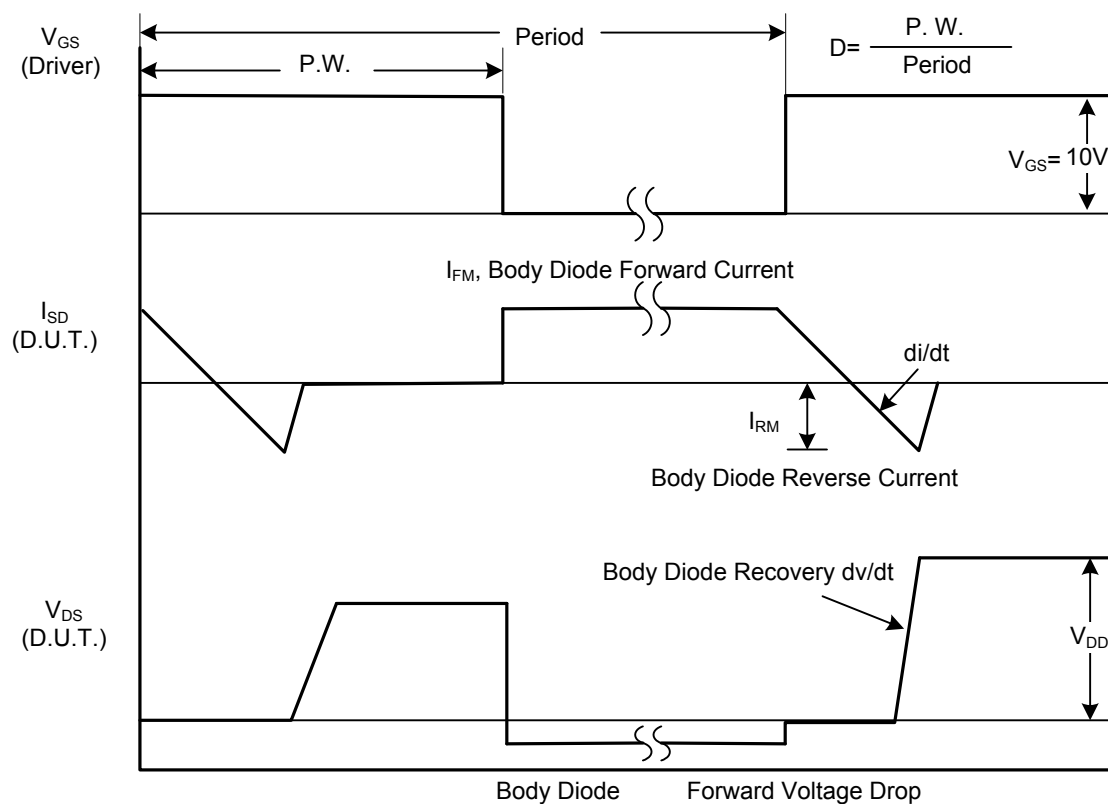
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

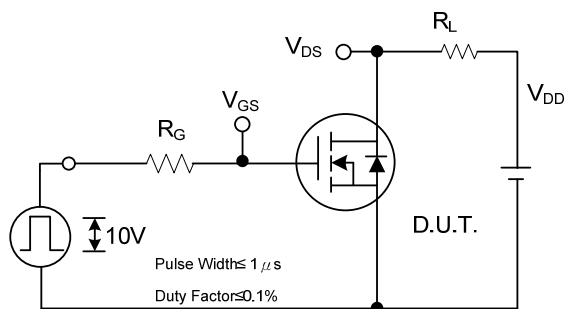


Peak Diode Recovery dv/dt Test Circuit

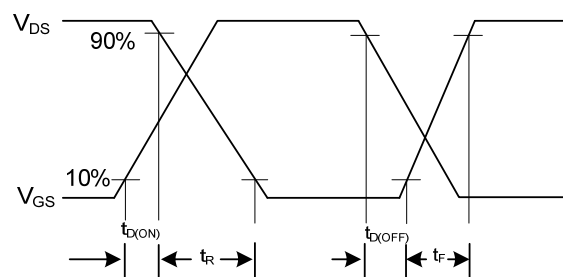


Peak Diode Recovery dv/dt Waveforms

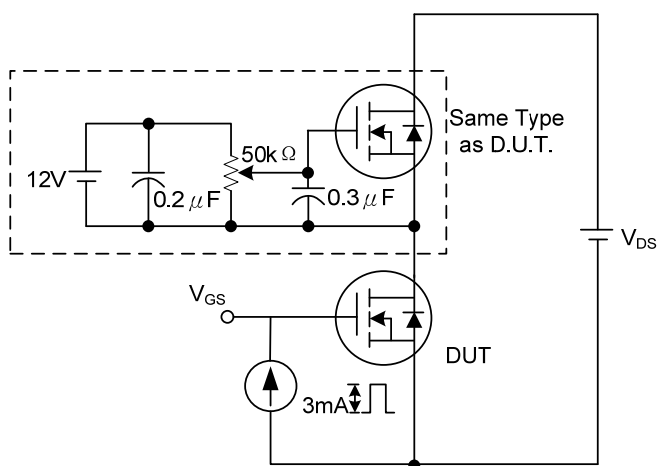
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



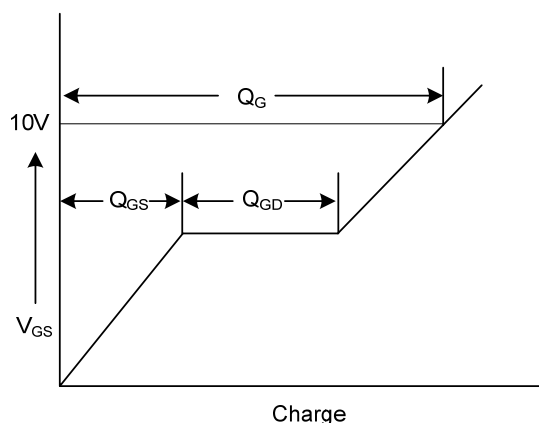
Switching Test Circuit



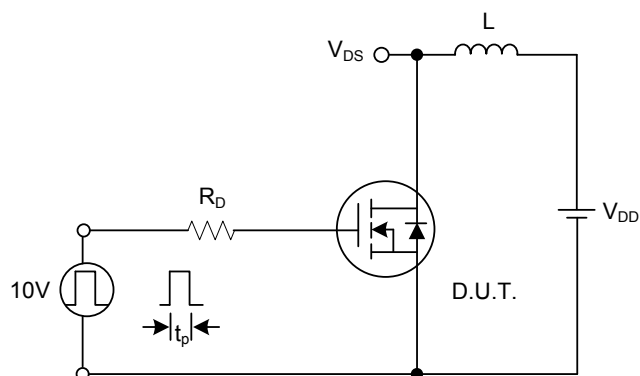
Switching Waveforms



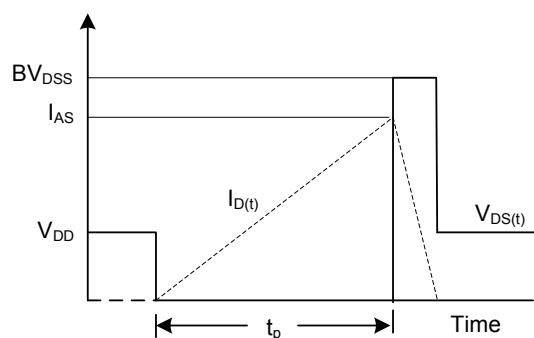
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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